

## Supporting Information

### Toward highly efficient photocatalysis: flow-through Pt@TiO<sub>2</sub>@AAO membrane nanoreactor prepared by atomic layer deposition

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#### Atomic layer deposition instruments for fabrication of TiO<sub>2</sub> film and Pt nanoparticles

1. TiO<sub>2</sub> Film (horizontal flow-type ALD, designed and constructed by Instrument Technology Research Center (ITRC), Taiwan and National Tsing Hua University (NTHU), Taiwan)

TiCl<sub>4</sub> and H<sub>2</sub>O were used as precursors. The purge times of TiCl<sub>4</sub> and H<sub>2</sub>O were 0.4 s and 0.2 s, respectively. All precursor pulses were separated by 5 s of N<sub>2</sub> purge. Precursors were kept equilibrium at room temperature (~25 °C). No carrier gas was applied. The substrate temperature was 100 °C and working pressure was 2 mTorr. The growth rate was approximately 0.58 Å per cycle.

2. Pt Nanoparticles (vertical flow-type ALD, designed by Instrument Technology Research Center (ITRC), Taiwan and National Tsing Hua University (NTHU), Taiwan and constructed by SYSKEY Technology, Taiwan)

MeCpPtMe<sub>3</sub> and oxygen were used as precursors. MeCpPtMe<sub>3</sub> pulse (1 s) and O<sub>2</sub> pulse (5 s) were separated by 20 s of N<sub>2</sub> purge. Precursors were kept equilibrium at 80 °C. No carrier gas was applied. The Pt deposition was carried out for 50 cycles. Substrate temperature was kept at 350 °C.



Fig. 1 Photographs of the home-made ALD systems.